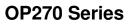
# Infrared Light Emitting Diode in SMD Plastic Package



- 880nm Wavelength
- Narrow Beam Angle
- High Power
- Four Lead Configurations
- 1.9mm Water Clear Plastic Package



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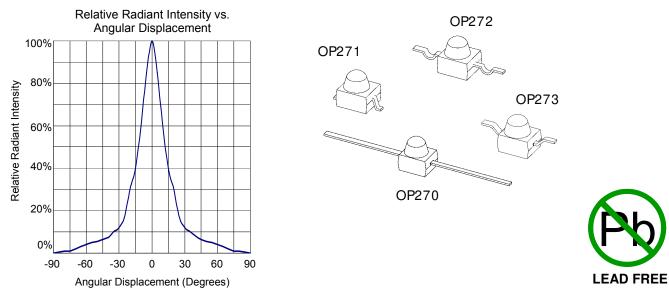
The OP270 series are GaAlAs infrared LEDs mounted in a clear plastic SMT packages. The devices incorporate an integral molded lens which enables a narrow beam angle and provides an even emission pattern. This series is available with four lead configurations and is compatible with most automated mounting equipment. The OP270 Series LEDs are mechanically and spectrally matched to the OP570 series phototransistors.

#### Applications

- Non-Contact Position Sensing
- Datum detection
- Machine automation

- Optical encoders
- IrDA
- Reflective and Transmissive Sensors

Part Number	Description	Material	Lead Style
OP270	LED, SMD, 1.9mm Molded	GaAlAs	Axial
OP271	LED, SMD, 1.9mm Molded	GaAlAs	Gull-Wing
OP272	LED, SMD, 1.9mm Molded	GaAlAs	Yoke Bend
OP273	LED, SMD, 1.9mm Molded	GaAlAs	Reverse Gull-Wing





Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.



## Absolute Maximum Ratings $T_A = 25^{\circ}$ C unless otherwise noted

Storage Temperature Range	-40° C to +85° C
Operating Temperature Range	-40° C to +85° C
Lead Soldering Temperature	260° C <sup>(1)</sup>
Reverse Voltage	30 V
Continuous Forward Current	50 mA
Power Dissipation	130 mW <sup>(2)</sup>

Notes:

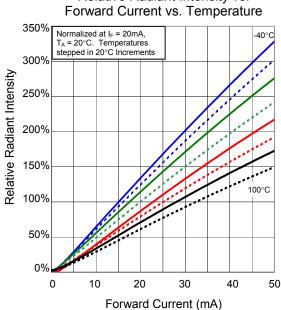
Solder time less than 5 seconds at temperature extreme. 1.

De-rate linearly at 2.17 mW/° C above 25° C. 2.

#### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

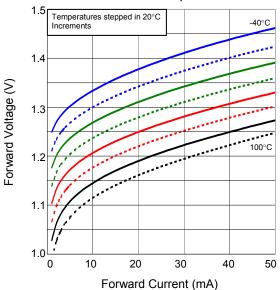
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	CONDITIONS
E <sub>e(APT)</sub>	Apertured Radiant Incidence	1.5			mW/cm <sup>2</sup>	I <sub>F</sub> = 20mA <sup>(3)</sup>
V <sub>F</sub>	Forward Voltage			1.5	V	I <sub>F</sub> = 20mA
I <sub>R</sub>	Reverse Current			100	μA	V <sub>R</sub> = 2.0V
λ <sub>P</sub>	Peak Emission Wavelength		890		nm	I <sub>F</sub> = 10mA
Θ <sub>ΗΡ</sub>	Emission Angle at Half Power Points		25		Deg.	I <sub>F</sub> = 20mA
t <sub>r</sub> , t <sub>f</sub>	Rise and Fall Time			500	ns	$I_{F(PEAK)}$ = 100mA, PW = 10µs, 10% D.C.

3. E<sub>e(APT)</sub> is a measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99mm) from the measurement surface. E<sub>e(APT)</sub> is not necessarily uniform within the measured area.



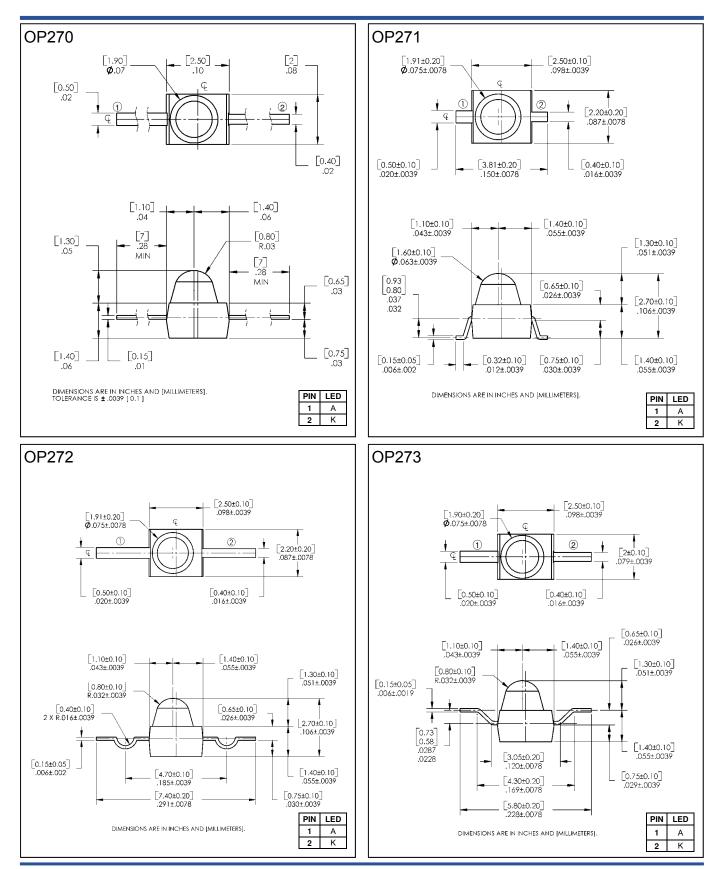
### Relative Radiant Intensity vs.

#### Forward Voltage vs. Forward Current vs. Temperature



#### SMD Infrared LED OP270 Series





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